

AMENDMENTS TO THE SPECIFICATION

Please replace paragraph [0017] with the following amended paragraph:

[0017] FIGS. 1A – 1B show a cross-sectional view of a process for treating a film structure containing a fluoro-carbon dielectric film in accordance with an embodiment of the invention. The film structure 1 contains a substrate 2 and a fluoro-carbon dielectric film 4 deposited onto the substrate 2. The fluoro-carbon dielectric film 4 can, for example, be a dense film with low or no porosity. In one example, the fluoro-carbon dielectric film can have dielectric constant between about 2.2 and about 2.4. Low porosity of the fluoro-carbon dielectric film 4 can reduce or eliminate various problems, such as moisture uptake and poor mechanical strength, which are commonly encountered for porous low-k films. The fluoro-carbon dielectric film 4 can, for example, be deposited on the substrate 2 in a plasma processing system using a process gas containing a halocarbon gas (e.g., C_5F_8) or $SiH(CH_3)_3$ [I]].